

CLAIMS

1. A continuous process for preparing a tablet comprising Compound 1 comprising the steps of:
 - a) mixing Compound 1, a filler, and a disintegrant in a blender to form a blend;
 - b) preparing a granulation solution with water, a binder, and a surfactant;
 - c) feeding the blend from step a) into a continuous twin screw granulator while adding the granulation solution from step b) to produce granules;
 - d) drying the granules from step c) and milling them;
 - e) blending the milled granules from step d) with a filler, disintegrant, and lubricant to form a blend; and
 - f) compressing the blend from step e) into a tablet;wherein Compound 1 is 3-(6-(1-(2,2-difluorobenzo[d][1,3]dioxol-5-yl) cyclopropanecarboxamido)-3-methylpyridin-2-yl)benzoic acid.
2. The process of claim 1, wherein the process further comprises the step of coating the tablet from step f).
3. The process of claim 2, wherein the tablet is coated with a film or a colorant.
4. The process of any one of claims 1 to 3, wherein Compound 1 (3-(6-(1-(2,2-difluorobenzo[d][1,3]dioxol-5-yl) cyclopropanecarboxamido)-3-methylpyridin-2-yl)benzoic acid) is in Form I, wherein the Form I is characterized by one or more peaks at 15.2 to 15.6 degrees, 16.1 to 16.5 degrees, and 14.3 to 14.7 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
5. The process of claim 4, wherein the particle size of Compound 1 Form I is between 0.1 and 10 microns.
6. The process of claim 4, wherein the particle size of Compound 1 Form I is between 1 and 5 microns.

7. The process of any one of claims 4 to 6, wherein Compound 1 Form I has a particle size D50 of 2.0 microns.
8. The process of any one of claims 4 to 7, wherein the tablet comprises at least 30 wt% by weight of Compound 1 Form I.
9. The process of any one of claims 1 to 8, wherein the tablet has a target friability of less than 1.0% after 400 revolutions.
10. The process of any one of claims 1 to 9, wherein the tablet has a hardness of at least 5 kP.
11. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by a peak having a 2θ value within the range of 16.1 to 16.5 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
12. The process of claim 11, wherein Compound 1 Form I is characterized by a peak having a 2θ value at 16.3 degrees in an X-ray powder diffraction.
13. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by a peak having a 2θ value within the range of 14.3 to 14.7 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
14. The process of claim 13, wherein Compound 1 Form I is characterized by a peak having a 2θ value at 14.5 degrees in an X-ray powder diffraction.
15. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by a peak having a 2θ value within the range of 15.2 to 15.6 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.

16. The process of claim 15, wherein Compound 1 Form I is characterized by a peak having a 2θ value at 15.4 degrees in an X-ray powder diffraction.
17. The process of any one of claims 11 to 16, wherein Compound 1 Form I is further characterized by a peak having a 2θ value within the range of 17.6 to 18.0 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
18. The process of any one of claims 11 to 17, wherein Compound 1 Form I is further characterized by a peak having a 2θ value within the range of 7.6 to 8.0 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
19. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by one or more peaks having a 2θ value selected from 14.41 ± 0.2 degrees, 14.64 ± 0.2 degrees, 15.23 ± 0.2 degrees, 16.11 ± 0.2 degrees, 17.67 ± 0.2 degrees, 19.32 ± 0.2 degrees, 21.67 ± 0.2 degrees, 23.40 ± 0.2 degrees, 23.99 ± 0.2 degrees, 26.10 ± 0.2 degrees, and 28.54 ± 0.2 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
20. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by one or more peaks having a 2θ value selected from 7.83 ± 0.2 degrees; 14.51 ± 0.2 degrees; 14.78 ± 0.2 degrees; 15.39 ± 0.2 degrees; 16.26 degrees; 16.62 ± 0.2 degrees; 17.81 ± 0.2 degrees; 21.59 ± 0.2 degrees; 23.32 ± 0.2 degrees; 24.93 ± 0.2 degrees; and 25.99 ± 0.2 degrees in an X-ray powder diffraction obtained using Cu K alpha radiation.
21. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by a diffraction pattern substantially similar to that of Figure 1.
22. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized by a diffraction pattern substantially similar to that of Figure 2.

23. The process of any one of claims 4 to 10, wherein Compound 1 Form I is characterized as a monoclinic crystal system in $P2_1/n$ space group with the following unit cell dimensions: $a=4.9626(7)$ Å, $b=12.299(2)$ Å, $c=33.075(4)$ Å, $\beta=93.938(9)^\circ$.